

# SiPM readout electronics

Albert Comerma (albert@ecm.ub.es)

Universitat de Barcelona

20<sup>th</sup> June 2011



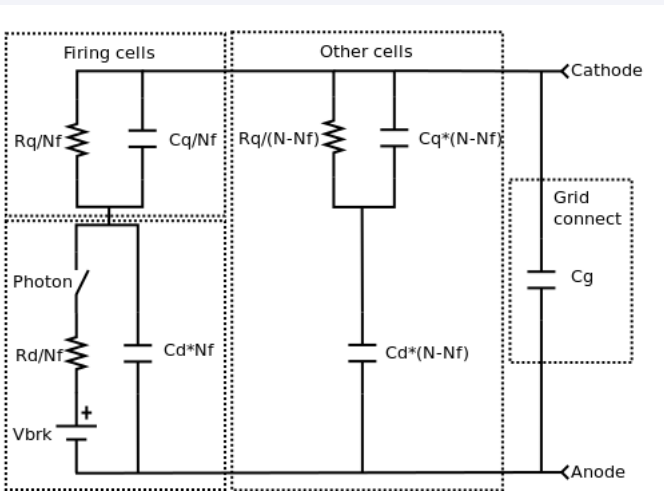
- Two main architectures used for SiPM readout;
  - Charge amplifier input.
  - Common base input and current mirroring.
- After first stage most solutions use different paths for timing (high bandwidth) and charge (limited bandwidth) information.
- For speed and power consumption seems to be better the common base input stage.
- Differential or single ended input are reasonable, but in the first case some external components are needed.
- Most designs use an input stage that can modify SiPM operation voltage by around 1V, to equalize gain and compensate temperature.
- Low input impedance is desirable to increase SiPM current signal at the input.

Design	Measurement	Aplication	Input	Techno	Year
<b>FLC_SiPM</b>	Charge	ILC	current	CMOS 0,8	2004
<b>MAROC2</b>	Charge, trig	ATLAS	current	SiGe 0,35	2006
<b>SPIROC</b>	Charge, trig, time	ILC	current	SiGe 0,35	2007
<b>NINO</b>	Trigger, pulse width	ALICE	differential	CMOS 0,25	2004
<b>PETA</b>	Charge, trig, time	PET	current	CMOS 0,18	2008
<b>BASIC</b>	Height, trig	PET	current	CMOS 0,35	2009
<b>VATA64</b>	Height, trig, time	RICH	current		2009
<b>RAPSODI</b>	Height, trig	SNOOPER	current	CMOS 0,35	2008

Design	Chans	Power <sup>1</sup>	Area <sup>2</sup>	Range	Rin	Digital out
<b>FLC_SiPM</b>	18	11	0.55			n
<b>MAROC2</b>	64	2	0.25	80pC	50Ω	y
<b>SPIROC</b>	36	2.5	0.89			y
<b>NINO</b>	8	30	1	2000pe	20Ω	n
<b>PETA</b>	40		0.625	8bit		y
<b>BASIC</b>	32	6.6	0.22	70pC	17Ω	y
<b>VATA64</b>	64	15	1	12pC		n
<b>RAPSODI</b>	2	100	4.5	100pC	20Ω	y

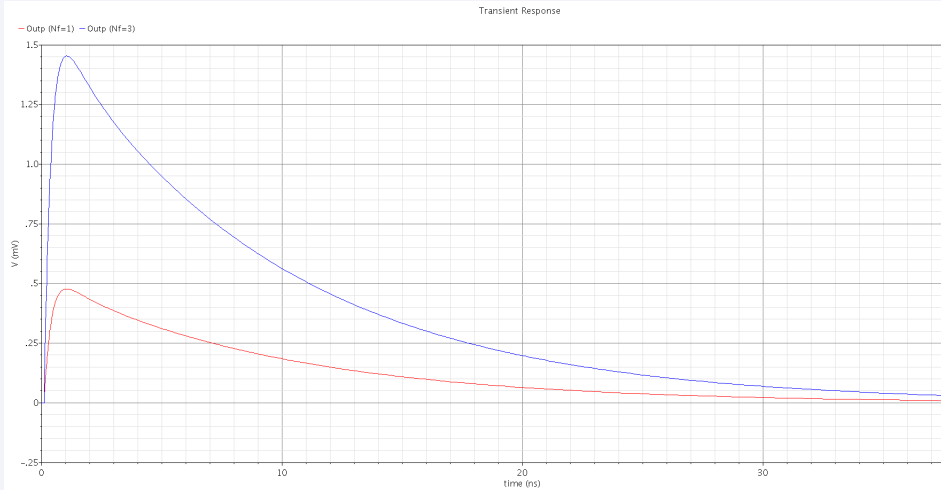
<sup>1</sup> Total power divided by number of channels without power down during idle times (mW).

<sup>2</sup> Total area divided by number of channels (mm<sup>2</sup>).



- R<sub>q</sub>** Quenching resistor value
- C<sub>q</sub>** Parasitic capacitance of R<sub>q</sub>
- N** Number of cells
- N<sub>f</sub>** Number of firing cells
- C<sub>d</sub>** Diode capacitance
- R<sub>d</sub>** Diode resistance
- V<sub>brk</sub>** Breakdown voltage
- C<sub>g</sub>** Grid connect capacitance

Parameters fixed to have a similar shape as in measurements;  
Peak of  $400 \frac{\mu\text{V}}{\text{cell}}$  and 20ns recharge time (with  $50\Omega$  load).



## Model used as input signals of the designed circuits:

